

## Amendments

### LISTING OF CLAIMS:

1. (Canceled)
2. (Currently amended) A ~~magneto-resistive~~ magnetoresistive random access memory comprising:

a vertical structure field effect transistor including; channel column and drain area sequentially ~~forms~~ formed on an insulation substrate; source area formed on the insulation substrate on which the channel column has not been formed, and read word lines formed at both sides of around the channel column to serve as a gate; and

a contact line, a magnetic tunnel junction cell, a bit line and a write word line sequentially formed on the drain area,

wherein the magnetic tunnel junction cell is aligned in a matrix shape through the self-alignment method by using a bit line mask and a word line mask, without requiring a special mask process for forming the patterns of the ~~magneto-resistive~~ magnetoresistive random access memory,[[.]]

wherein the magnetic tunnel junction cell is formed by sequentially stacking an anti-ferroelectric thin film, a pinned ferromagnetic thin film, an insulation layer and a free ferromagnetic thin film on the contact line.
3. (Previously presented) The magnetoresistive random access memory of claim 2, wherein the source area and the drain area are formed according to ion implantation, and the channel column is comprised of silicon.
4. (Previously presented) The magnetoresistive random access memory of claim 2, wherein the read word line is formed by depositing polysilicon.
5. (Canceled)
- 6-13. (Canceled)